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This document, MC74HC4051/D has been canceled and replaced by MC74HC4051A/D LAN was sent 9/28/01

Analog Multiplexers/ Demultiplexers

High-Performance Silicon-Gate CMOS

The MC54/74HC4051, MC74HC4052 and MC54/74HC4053 utilize silicon–gate CMOS technology to achieve fast propagation delays, low ON resistances, and low OFF leakage currents. These analog multiplexers/demultiplexers control analog voltages that may vary across the complete power supply range (from V_{CC} to V_{EE}).

The HC4051, HC4052 and HC4053 are identical in pinout to the metal–gate MC14051B, MC14052B and MC14053B. The Channel–Select inputs determine which one of the Analog Inputs/Outputs is to be connected, by means of an analog switch, to the Common Output/Input. When the Enable pin is HIGH, all analog switches are turned off.

The Channel–Select and Enable inputs are compatible with standard CMOS outputs; with pullup resistors they are compatible with LSTTL outputs.

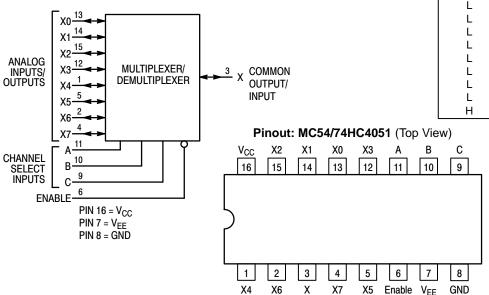
These devices have been designed so that the ON resistance (R_{on}) is more linear over input voltage than R_{on} of metal-gate CMOS analog switches.

For multiplexers/demultiplexers with channel–select latches, see HC4351, HC4352 and HC4353.

- · Fast Switching and Propagation Speeds
- Low Crosstalk Between Switches
- Diode Protection on All Inputs/Outputs
- Analog Power Supply Range (V_{CC} V_{EE}) = 2.0 to 12.0 V
- Digital (Control) Power Supply Range (V_{CC} GND) = 2.0 to 6.0 V
- Improved Linearity and Lower ON Resistance Than Metal–Gate Counterparts
- Low Noise
- In Compliance With the Requirements of JEDEC Standard No. 7A
- Chip Complexity: HC4051 184 FETs or 46 Equivalent Gates HC4052 — 168 FETs or 42 Equivalent Gates

HC4053 — 156 FETs or 39 Equivalent Gates

LOGIC DIAGRAM MC54/74HC4051 Single-Pole, 8-Position Plus Common Off



MC54/74HC4051 MC74HC4052 MC54/74HC4053



J SUFFIX

CERAMIC PACKAGE CASE 620-10



N SUFFIX

PLASTIC PACKAGE CASE 648-08



D SUFFIX

SOIC PACKAGE CASE 751B-05



DW SUFFIX

SOIC PACKAGE CASE 751G-02



DT SUFFIX

TSSOP PACKAGE CASE 948F-01

ORDERING INFORMATION

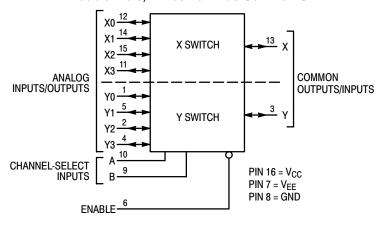
MC54HCXXXXJ Ceramic
MC74HCXXXXN Plastic
MC74HCXXXXD SOIC
MC74HCXXXXDW SOIC Wide
MC74HCXXXXDT TSSOP

FUNCTION TABLE - MC54/74HC4051

Contr	ol Inp			
Enable	Select C B A			ON Channels
L	L	L	L	X0
L	L	L	Н	X1
L	L	Н	L	X2
L	L	Н	Н	X3
L	Н	L	L	X4
L	Н	L	Н	X5
L	Н	Н	L	X6
L	Н	Н	Н	X7
Н	Х	Χ	Χ	NONE

X = Don't Care

LOGIC DIAGRAM MC74HC4052 Double-Pole, 4-Position Plus Common Off

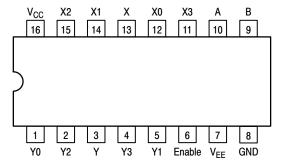


FUNCTION TABLE - MC74HC4052

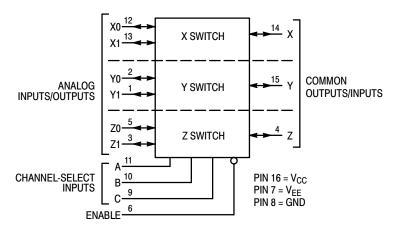
Contr	ol Input				
Select Enable B A			ON Ch	annels	
L L L	L L H	L H L	Y0 Y1 Y2 Y3	X0 X1 X2 X3	
H	X	Χ	NONE		

X = Don't Care

Pinout: MC74HC4052 (Top View)



LOGIC DIAGRAM MC54/74HC4053 Triple Single-Pole, Double-Position Plus Common Off



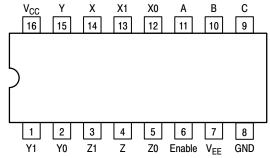
NOTE: This device allows independent control of each switch. Channel–Select Input A controls the X–Switch, Input B controls the Y–Switch and Input C controls the Z–Switch

FUNCTION TABLE - MC54/74HC4053

Control Inputs						
Select Enable C B A				10	N Chann	els
L L L L		L H H L H	L H L H L H X	Z0 Z0 Z0 Z0 Z1 Z1 Z1 Z1 Z1	Y0 Y0 Y1 Y1 Y1 Y0 Y0 Y1 Y1	X0 X1 X0 X1 X0 X1 X0 X1

X = Don't Care

Pinout: MC54/74HC4053 (Top View)



MC54/74HC4051 MC74HC4052 MC54/74HC4053

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V _{CC}	Positive DC Supply Voltage (Referenced to GND) (Referenced to V _{EE})	- 0.5 to + 7.0 - 0.5 to + 14.0	V
V _{EE}	Negative DC Supply Voltage (Referenced to GND)	- 7.0 to + 5.0	V
V _{IS}	Analog Input Voltage	$V_{EE} - 0.5 \text{ to} $ $V_{CC} + 0.5$	٧
V _{in}	Digital Input Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
I	DC Current, Into or Out of Any Pin	± 25	mA
P _D	Power Dissipation in Still Air, Plastic or Ceramic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T _{stg}	Storage Temperature Range	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds Plastic DIP, SOIC or TSSOP Package Ceramic DIP	260 300	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

†Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C Ceramic DIP: – 10 mW/°C from 100° to 125°C SOIC Package: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V _{CC}	Positive DC Supply Voltage	(Referenced to GND) (Referenced to V _{EE})	2.0 2.0	6.0 12.0	V
V _{EE}	Negative DC Supply Voltage, Outp GND)	gative DC Supply Voltage, Output (Referenced to D)			٧
V _{IS}	Analog Input Voltage			V _{CC}	V
V _{in}	Digital Input Voltage (Referenced t	o GND)	GND	V _{CC}	V
V _{IO} *	Static or Dynamic Voltage Across	Switch		1.2	V
T _A	Operating Temperature Range, All Package Types			+ 125	°C
t _r , t _f	Input Rise/Fall Time (Channel Select or Enable Input	$V_{CC} = 2.0 \text{ V}$ s) $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$	0 0 0	1000 500 400	ns

^{*} For voltage drops across switch greater than 1.2V (switch on), excessive V_{CC} current may be drawn; i.e., the current out of the switch may contain both V_{CC} and switch input components. The reliability of the device will be unaffected unless the Maximum Ratings are exceeded.

^{*} Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.

$\textbf{DC CHARACTERISTICS} \ -- \ \textbf{Digital Section} \ (\textit{Voltages Referenced to GND}) \ \textit{V}_{\textit{EE}} = \textit{GND}, \ \textit{Except Where Noted} \$

			V _{CC}	Guara	nteed Lim	nit	
Symbol	Parameter	Condition	v	–55 to 25°C	≤85°C	≤125°C	Unit
V _{IH}	Minimum High–Level Input Voltage, Channel–Select or Enable Inputs	R _{on} = Per Spec	2.0 4.5 6.0	1.50 3.15 4.20	1.50 3.15 4.20	1.50 3.15 4.20	V
V _{IL}	Maximum Low–Level Input Voltage, Channel–Select or Enable Inputs	R _{on} = Per Spec	2.0 4.5 6.0	0.3 0.9 1.2	0.3 0.9 1.2	0.3 0.9 1.2	V
I _{in}	Maximum Input Leakage Current, Channel–Select or Enable Inputs	$V_{in} = V_{CC}$ or GND, $V_{EE} = -6.0 \text{ V}$	6.0	± 0.1	± 1.0	± 1.0	μА
Icc	Maximum Quiescent Supply Current (per Package)		= GND 6.0 = - 6.0 6.0	2 8	20 80	40 160	μΑ

DC CHARACTERISTICS — Analog Section

					Guara	nteed Lim	nit	
Symbol	Parameter	Condition	V _{CC}	V _{EE}	–55 to 25°C	≤85°C	≤125°C	Unit
R _{on}	Maximum "ON" Resistance	$V_{in} = V_{IL}$ or V_{IH} ; $V_{IS} = V_{CC}$ to V_{EE} ; $I_S \le 2.0$ mA (Figures 1, 2)	4.5 4.5 6.0	0.0 - 4.5 - 6.0	190 120 100	240 150 125	280 170 140	Ω
		$V_{\text{in}} = V_{\text{IL}}$ or V_{IH} ; $V_{\text{IS}} = V_{\text{CC}}$ or V_{EE} (Endpoints); $I_{\text{S}} \le 2.0$ mA (Figures 1, 2)	4.5 4.5 6.0	0.0 - 4.5 - 6.0	150 100 80	190 125 100	230 140 115	
ΔR_{on}	Maximum Difference in "ON" Resistance Between Any Two Channels in the Same Package	$V_{in} = V_{IL} \text{ or } V_{IH};$ $V_{IS} = 1/2 (V_{CC} - V_{EE});$ $I_S \le 2.0 \text{ mA}$	4.5 4.5 6.0	0.0 - 4.5 - 6.0	30 12 10	35 15 12	40 18 14	Ω
l _{off}	Maximum Off–Channel Leakage Current, Any One Channel	$V_{in} = V_{IL} \text{ or } V_{IH};$ $V_{IO} = V_{CC} - V_{EE};$ Switch Off (Figure 3)	6.0	- 6.0	0.1	0.5	1.0	μА
	Maximum Off–Channel HC4051 Leakage Current, HC4052 Common Channel HC4053	$V_{in} = V_{IL} \text{ or } V_{IH};$ $V_{IO} = V_{CC} - V_{EE};$ Switch Off (Figure 4)	6.0 6.0 6.0	- 6.0 - 6.0 - 6.0	0.2 0.1 0.1	2.0 1.0 1.0	4.0 2.0 2.0	
I _{on}	Maximum On–Channel HC4051 Leakage Current, HC4052 Channel–to–Channel HC4053	$V_{in} = V_{IL}$ or V_{IH} ; Switch-to-Switch = $V_{CC} - V_{EE}$; (Figure 5)	6.0 6.0 6.0	- 6.0 - 6.0 - 6.0	0.2 0.1 0.1	2.0 1.0 1.0	4.0 2.0 2.0	μΑ

MC54/74HC4051 MC74HC4052 MC54/74HC4053

AC CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

			v _{cc}	Gua	aranteed Lim	it	
Symbol	Parameter		٧	–55 to 25°C	≤85°C	≤125°C	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Channel–Select to Ana (Figure 9)	log Output	2.0 4.5 6.0	370 74 63	465 93 79	550 110 94	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Analog Input to Analog (Figure 10)	Output	2.0 4.5 6.0	60 12 10	75 15 13	90 18 15	ns
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, Enable to Analog Outp (Figure 11)	ut	2.0 4.5 6.0	290 58 49	364 73 62	430 86 73	ns
t _{PZL} , t _{PZH}	Maximum Propagation Delay, Enable to Analog Outp (Figure 11)	ut	2.0 4.5 6.0	345 69 59	435 87 74	515 103 87	ns
C _{in}	Maximum Input Capacitance, Channel-Select or Ena	ble Inputs		10	10	10	pF
C _{I/O}	Maximum Capacitance	Analog I/O		35	35	35	pF
	(All Switches Off) Common	O/I: HC4051 HC4052 HC4053		130 80 50	130 80 50	130 80 50	
		Feedthrough		1.0	1.0	1.0	

Ī				Typical @ 25° C, $V_{CC} = 5.0 \text{ V}$, $V_{EE} = 0 \text{ V}$	
	C _{PD}	Power Dissipation Capacitance (Figure 13)*	HC4051 HC4052 HC4053	45 80 45	pF

ADDITIONAL APPLICATION CHARACTERISTICS (GND = 0 V)

			V _{CC}	VEE		Limit*		
Symbol	Parameter	Condition		V		25°C		Unit
BW	Maximum On–Channel Bandwidth or Minimum Frequency Response (Figure 6)	$\begin{aligned} &f_{in} = \text{1MHz Sine Wave; Adjust } f_{in} \text{ Voltage to} \\ &\text{Obtain 0dBm at V}_{OS}; \text{ Increase } f_{in} \text{ Frequency} \\ &\text{Until dB Meter Reads } -3\text{dB;} \\ &R_L = 50\Omega, \ C_L = 10\text{pF} \end{aligned}$	2.25 4.50 6.00	-2.25 -4.50 -6.00	'51 80 80 80	52 95 95 95	'53 120 120 120	MHz
_	Off–Channel Feedthrough Isolation (Figure 7)	f_{in} = Sine Wave; Adjust f_{in} Voltage to Obtain 0dBm at V _{IS} f_{in} = 10kHz, R _L = 600 Ω , C _L = 50pF	2.25 4.50 6.00	-2.25 -4.50 -6.00		-50 -50 -50		dB
		$f_{in} = 1.0MHz, R_L = 50\Omega, C_L = 10pF$	2.25 4.50 6.00	-2.25 -4.50 -6.00		-40 -40 -40		
_	Feedthrough Noise. Channel–Select Input to Common I/O (Figure 8)	$\begin{aligned} &V_{in} \leq \text{1MHz Square Wave } (t_f = t_f = 6\text{ns}); \\ &\text{Adjust R}_L \text{ at Setup so that } I_S = 0\text{A}; \\ &\text{Enable} = \text{GND} & \text{R}_L = 600\Omega, \text{ C}_L = 50\text{pF} \end{aligned}$	2.25 4.50 6.00	-2.25 -4.50 -6.00		25 105 135		mV_{PP}
		$R_L = 10k\Omega$, $C_L = 10pF$	2.25 4.50 6.00	-2.25 -4.50 -6.00		35 145 190		
_	Crosstalk Between Any Two Switches (Figure 12) (Test does not apply to HC4051)	f_{in} = Sine Wave; Adjust f_{in} Voltage to Obtain 0dBm at V _{IS} f_{in} = 10kHz, R _L = 600 Ω , C _L = 50pF	2.25 4.50 6.00	-2.25 -4.50 -6.00		-50 -50 -50		dB
		f_{in} = 1.0MHz, R_L = 50 Ω , C_L = 10pF	2.25 4.50 6.00	-2.25 -4.50 -6.00		-60 -60 -60		
THD	Total Harmonic Distortion (Figure 14)	$\begin{split} f_{in} = 1 \text{kHz, } R_L = 10 \text{k}\Omega, C_L = 50 \text{pF} \\ \text{THD} = \text{THD}_{measured} - \text{THD}_{source} \\ V_{IS} = 4.0 \text{V}_{PP} \text{ sine wave} \\ V_{IS} = 8.0 \text{V}_{PP} \text{ sine wave} \\ V_{IS} = 11.0 \text{V}_{PP} \text{ sine wave} \end{split}$	2.25 4.50 6.00	-2.25 -4.50 -6.00		0.10 0.08 0.05		%

^{*} Limits not tested. Determined by design and verified by qualification.

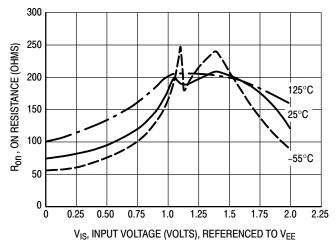


Figure 1a. Typical On Resistance, $V_{CC} - V_{EE} = 2.0 \text{ V}$

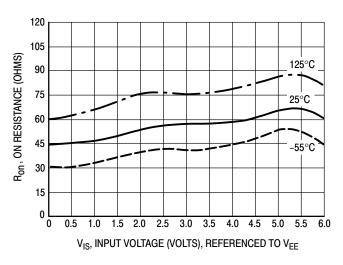


Figure 1c. Typical On Resistance, $V_{CC} - V_{EE} = 6.0 \text{ V}$

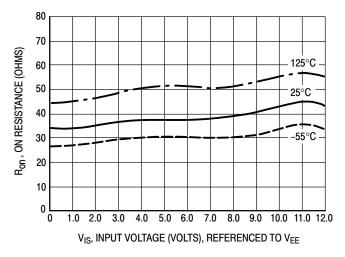


Figure 1e. Typical On Resistance, $V_{CC} - V_{EE} = 12.0 \text{ V}$

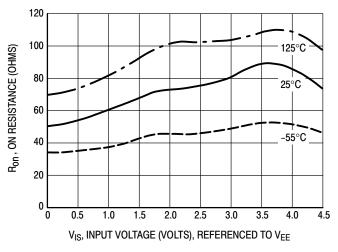


Figure 1b. Typical On Resistance, $V_{CC} - V_{EE} = 4.5 \text{ V}$

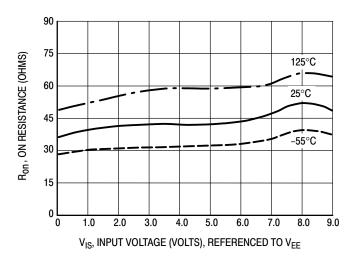


Figure 1d. Typical On Resistance, $V_{CC} - V_{EE} = 9.0 \text{ V}$

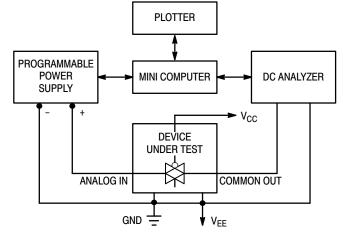


Figure 2. On Resistance Test Set-Up

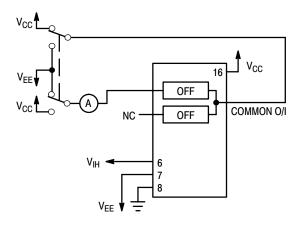


Figure 3. Maximum Off Channel Leakage Current, Any One Channel, Test Set-Up

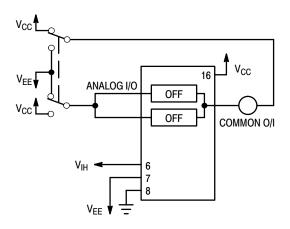


Figure 4. Maximum Off Channel Leakage Current, Common Channel, Test Set-Up

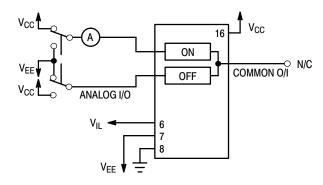


Figure 5. Maximum On Channel Leakage Current, Channel to Channel, Test Set-Up

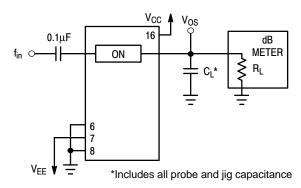
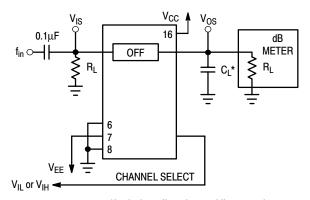
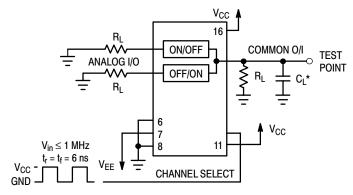


Figure 6. Maximum On Channel Bandwidth, Test Set-Up



*Includes all probe and jig capacitance

Figure 7. Off Channel Feedthrough Isolation, Test Set-Up



*Includes all probe and jig capacitance

Figure 8. Feedthrough Noise, Channel Select to Common Out, Test Set-Up

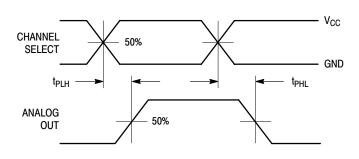
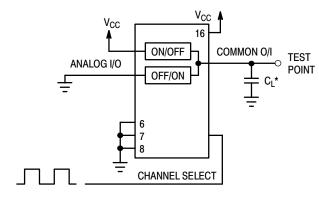


Figure 9a. Propagation Delays, Channel Select to Analog Out



*Includes all probe and jig capacitance

Figure 9b. Propagation Delay, Test Set-Up Channel Select to Analog Out

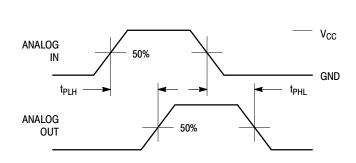
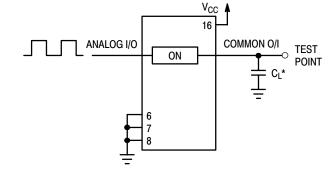


Figure 10a. Propagation Delays, Analog In to Analog Out



*Includes all probe and jig capacitance

Figure 10b. Propagation Delay, Test Set-Up Analog In to Analog Out

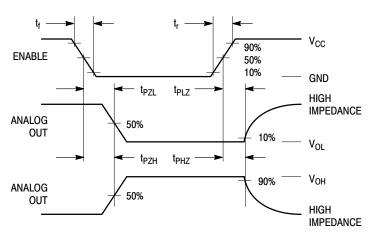


Figure 11a. Propagation Delays, Enable to Analog Out

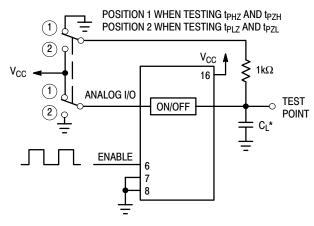


Figure 11b. Propagation Delay, Test Set-Up Enable to Analog Out

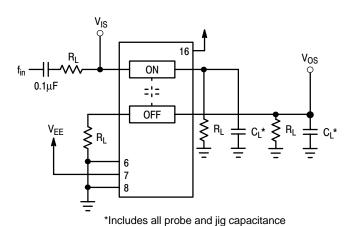


Figure 12. Crosstalk Between Any Two Switches, Test Set-Up

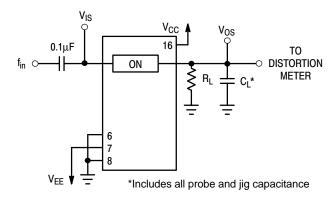


Figure 14a. Total Harmonic Distortion, Test Set-Up

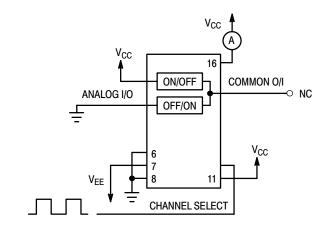


Figure 13. Power Dissipation Capacitance, Test Set-Up

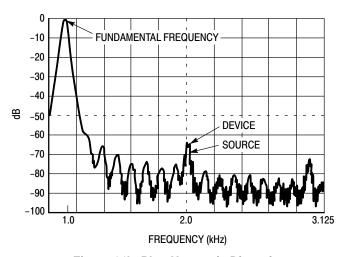


Figure 14b. Plot, Harmonic Distortion

APPLICATIONS INFORMATION

The Channel Select and Enable control pins should be at V_{CC} or GND logic levels. V_{CC} being recognized as a logic high and GND being recognized as a logic low. In this example:

$$V_{CC} = +5V = logic high$$

 $GND = 0V = logic low$

The maximum analog voltage swings are determined by the supply voltages V_{CC} and V_{EE} . The positive peak analog voltage should not exceed V_{CC} . Similarly, the negative peak analog voltage should not go below V_{EE} . In this example, the difference between V_{CC} and V_{EE} is ten volts. Therefore, using the configuration of Figure 15, a maximum analog signal of ten volts peak—to—peak can be controlled. Unused analog inputs/outputs may be left floating (i.e., not connected). However, tying unused analog inputs and outputs to

 $\rm V_{CC}$ or GND through a low value resistor helps minimize crosstalk and feedthrough noise that may be picked up by an unused switch.

Although used here, balanced supplies are not a requirement. The only constraints on the power supplies are that:

$$\begin{split} &V_{CC}-\text{GND}=2\text{ to 6 volts}\\ &V_{EE}-\text{GND}=0\text{ to }-6\text{ volts}\\ &V_{CC}-V_{EE}=2\text{ to }12\text{ volts}\\ &\text{and }V_{EE}\leq\text{GND} \end{split}$$

When voltage transients above V_{CC} and/or below V_{EE} are anticipated on the analog channels, external Germanium or Schottky diodes (D_x) are recommended as shown in Figure 16. These diodes should be able to absorb the maximum anticipated current surges during clipping.

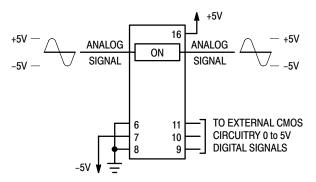


Figure 15. Application Example

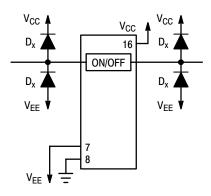
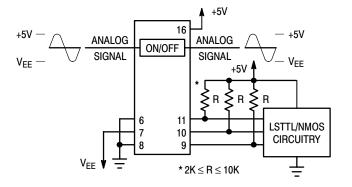
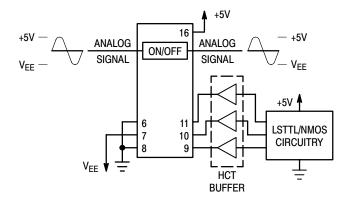


Figure 16. External Germanium or Schottky Clipping Diodes

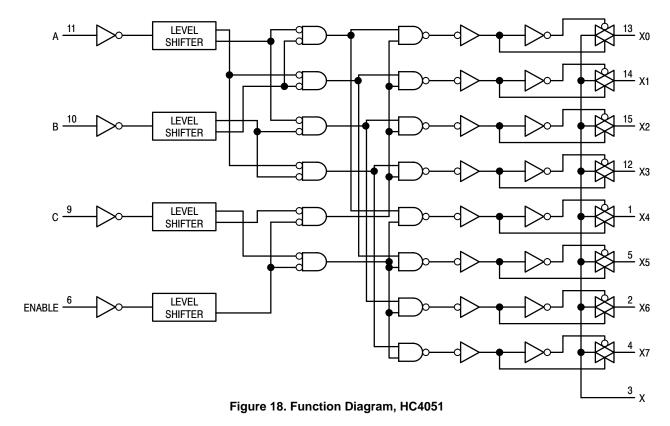






b. Using HCT Interface

Figure 17. Interfacing LSTTL/NMOS to CMOS Inputs



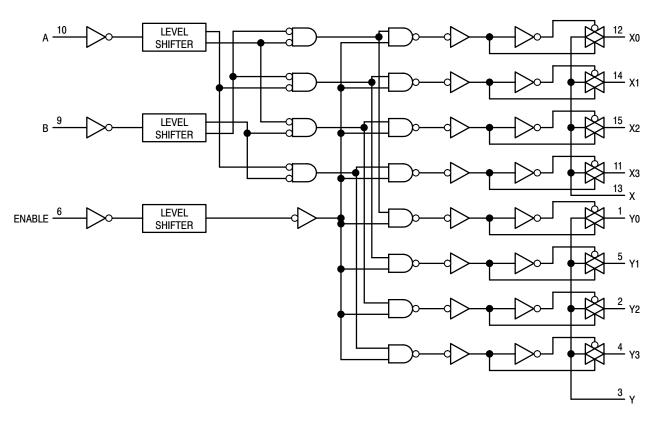


Figure 19. Function Diagram, HC4052

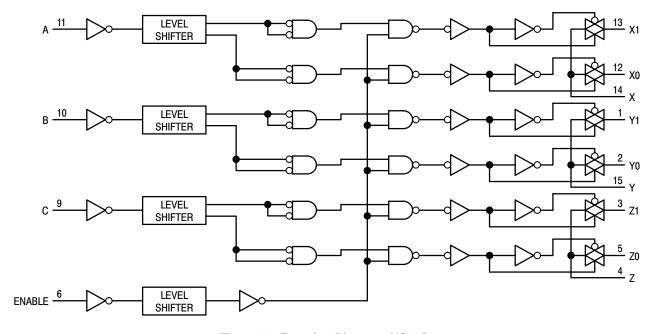
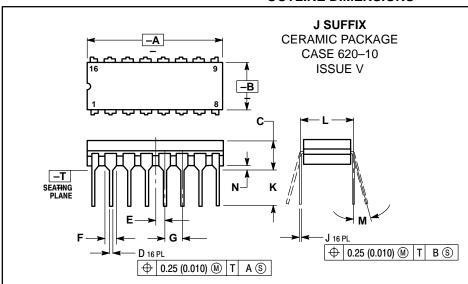


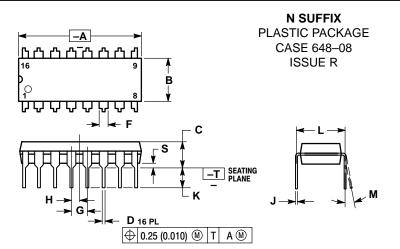
Figure 20. Function Diagram, HC4053

OUTLINE DIMENSIONS



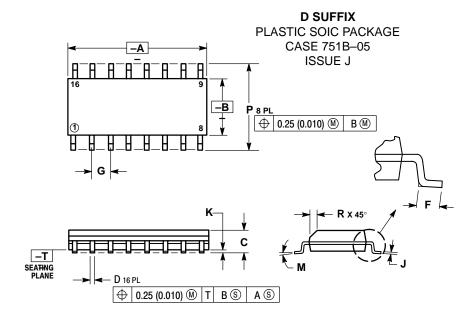
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 DIMENSION L TO CENTER OF LEAD WHEN
- FORMED PARALLEL
 DIM F MAY NARROW TO 0.76 (0.030) WHERE
 THE LEAD ENTERS THE CERAMIC BODY.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.750	0.785	19.05	19.93
В	0.240	0.295	6.10	7.49
С	_	0.200	_	5.08
D	0.015	0.020	0.39	0.50
E	0.050	BSC	1.27	BSC
F	0.055	0.065	1.40	1.65
G	0.100	BSC	2.54	BSC
J	0.008	0.015	0.21	0.38
K	0.125	0.170	3.18	4.31
L	0.300	BSC	7.62 BSC	
М	0°	15°	0° 15°	
N	0.020	0.040	0.51	1.01



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- DIMENSION L TO CENTER OF LEADS WHEN
- FORMED PARALLEL.
 DIMENSION B DOES NOT INCLUDE MOLD FLASH.
 ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.740	0.770	18.80	19.55
В	0.250	0.270	6.35	6.85
С	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.070	1.02	1.77
G	0.	100 BSC	2	.54 BSC
Н	0.	050 BSC	1	.27 BSC
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0°	10°	0°	10°
S	0.020	0.040	0.51 1.0	



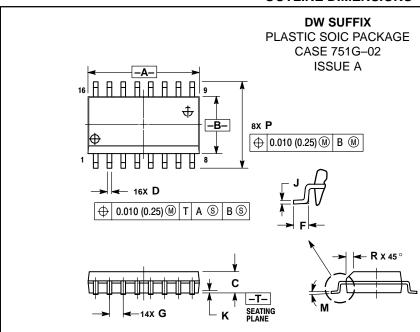
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- PER SIDE.

 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

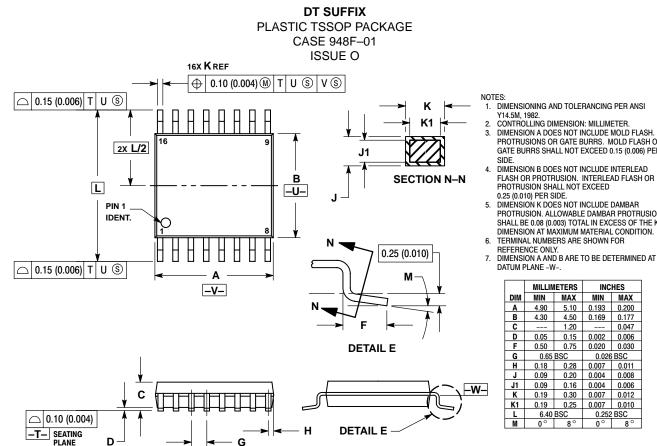
DIM MIN MA A 9.80 10.0 B 3.80 4.0 C 1.35 1.7 D 0.35 0.4 F 0.40 1.2 G 1.27 BSC	0 0.386 0 0.150	0.393 0.157
B 3.80 4.0 C 1.35 1.7 D 0.35 0.4 F 0.40 1.2	0 0.150	
C 1.35 1.7 D 0.35 0.4 F 0.40 1.2		0.157
D 0.35 0.4 F 0.40 1.2	0.054	
F 0.40 1.2	0.004	0.068
. 01.10	9 0.014	0.019
1 27 RS(0.049
G 1.27 D30	0.0	50 BSC
J 0.19 0.2	5 0.008	0.009
K 0.10 0.2	5 0.004	0.009
M 0° 7	° 0°	7°
P 5.80 6.2	- 1	0.244
R 0.25 0.5	0.229	0.019

OUTLINE DIMENSIONS



- DIMENSIONING AND TOLERANCING
- PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 DIMENSION D DOES NOT INCLUDE DAMBAR
- 5. PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.13 (0.005) TOTAL IN
 EXCESS OF D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	10.15	10.45	0.400	0.411	
В	7.40	7.60	0.292	0.299	
С	2.35	2.65	0.093	0.104	
D	0.35	0.49	0.014	0.019	
F	0.50	0.90	0.020	0.035	
G	1.27 BSC		0.050 BSC		
J	0.25	0.32	0.010	0.012	
K	0.10	0.25	0.004	0.009	
M	0 °	7°	0 °	7°	
P	10.05	10.55	0.395	0.415	
R	0.25	0.75	0.010	0.029	



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M. 1982.
- PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER
- DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
C		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

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